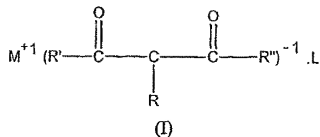


Amendments to the Claims:

1. (Currently Amended) A compound, ~~characterized in that it corresponds~~ corresponding to formula (I) below:

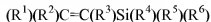


in which

- M represents a copper atom or silver atom;
- R' and R'', which may be identical or different, represent a group chosen from: a C₁-C₈ alkyl; an -OR''' group, in which R''' represents a C₁-C₈ alkyl;
- R represents a group chosen from: an -OR'''' group, in which R'''' represents a C₁-C₈ alkyl; a nitro group: NO₂; an aldehyde function: -CHO; a -COOR'''' ester function, in which R'''' represents a C₁-C₈ alkyl group;
- L represents a stabilizing ligand.

2. (Currently Amended) A compound according to formula (I), ~~characterized in that of~~ claim 1, wherein L is chosen from:

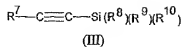
- a- carbon monoxide,
- b- unsaturated hydrocarbon-based ligands containing at least one nonaromatic unsaturation,
- c- isonitriles,
- d- phosphines,
- e- the compounds corresponding to formula (II) below:



in which

- R¹ represents the hydrogen atom or a C₁-C₈ alkyl group or an SiR⁴R⁵R⁶ group,
- R² and R³, which may be identical or different, represent the hydrogen atom or a C₁-C₈ alkyl group,
- R⁴, R⁵ and R⁶, which may be identical or different, represent a phenyl or C₁-C₈ alkyl group;

f- the compounds corresponding to formula (III) below:

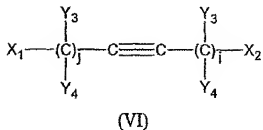
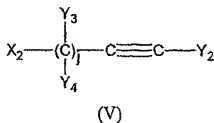
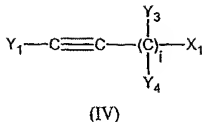


in which

- R^7 represents a $\text{C}_1\text{-C}_8$ alkyl, phenyl or $\text{Si}(\text{R}^8)_i(\text{R}^9)_j(\text{R}^{10})_k$ group,
- R^8 , R^9 and R^{10} , which may be identical or different, represent a $\text{C}_1\text{-C}_8$ alkyl or phenyl group,

phenyl group,

g- the compounds corresponding to one of the formulae (IV), (V) and (VI) below:



in which Y_1 , Y_2 , Y_3 and Y_4 , which may be identical or different, are chosen from a hydrogen atom, a $\text{C}_1\text{-C}_8$ alkyl and an $-\text{Si}(\text{R}_5)_3$ group where R_5 is a $\text{C}_1\text{-C}_8$ alkyl, i and j represent an integer chosen from 0, 1, 2 and 3, and X_1 and X_2 , which may be identical or different, represent an electron-withdrawing group, such as in particular a $\text{C}_1\text{-C}_8$ alkenyl.

3. (Previously Presented) A compound as claimed in claim 1, wherein M represents the copper atom.

4. (Previously Presented) A compound as claimed in claim 1, wherein R' or R'' represents a group chosen from CH₃ and C₂H₅.

5. (Previously Presented) A compound as claimed claim 1, wherein R represents a group chosen from NO₂ and OCH₃.

6. (Previously Presented) A compound as claimed in claim 1, wherein L represents a ligand chosen from 1,5-cyclooctadiene and bis(trimethylsilyl)acetylene.

7. (Currently Amended) A process method for the gas-phase chemical deposition of a metal chosen from copper and silver, on a support, ~~this process being characterized in that a compound as claimed in claim 1 is used as~~ wherein said method comprises the step consisting of applying a gas-phase deposition to a copper precursor or silver precursor according to claim 1.

8. (Currently Amended) The process method as claimed in claim 7, wherein the support consists of a material chosen from Si, AsGa, InP, SiC and SiGe.

9. (Currently Amended) The process method as claimed in claim 7, wherein the support contains one or more intermediate layers consisting of at least one material chosen from TiN, TiSiN, Ta, TaN, TaSiN, WN and WSiN.

10. (Currently Amended) The process method as claimed in claim 7, wherein ~~it~~ the gas-phase chemical deposition is carried out at a temperature ranging from 120 to 300°C.

11. (Currently Amended) The process method as claimed in claim 7, wherein the copper precursor or silver precursor is used pure.

12. (Currently Amended) The process method as claimed in claim 7, wherein the copper precursor or silver precursor is used in solution in a solvent.

13. (Currently Amended) ~~The use of a process as claimed in claim 7;~~ A method for depositing a layer of copper or of silver having a thickness ranging from 0.2 to 500 nm, wherein said method includes a method according to claim 7.

14. (Currently Amended) ~~The use of a process as claimed in claim 7, for producing~~ A method of production of an integrated circuit, wherein said method includes a method according to claim 7.